

Reet Chaudhuri

List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

19
papers

319
citations

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g-index

21
ext. papers

407
ext. citations

4.4
avg, IF

3.76
L-index

#	Paper	IF	Citations
19	A polarization-induced 2D hole gas in undoped gallium nitride quantum wells. <i>Science</i> , 2019 , 365, 1454-1457	35.3	57
18	High Breakdown Voltage in RF AlN/GaN/AlN Quantum Well HEMTs. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1293-1296	4.4	46
17	Gate-Recessed E-mode p-Channel HFET With High On-Current Based on GaN/AlN 2D Hole Gas. <i>IEEE Electron Device Letters</i> , 2018 , 39, 1848-1851	4.4	46
16	Prospects for Wide Bandgap and Ultrawide Bandgap CMOS Devices. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 4010-4020	2.9	38
15	Next generation electronics on the ultrawide-bandgap aluminum nitride platform. <i>Semiconductor Science and Technology</i> , 2021 , 36, 044001	1.8	17
14	GaN/AlN Schottky-gate p-channel HFETs with InGaN contacts and 100 mA/mm on-current 2019 ,		17
13	First RF Power Operation of AlN/GaN/AlN HEMTs With >3 A/mm and 3 W/mm at 10 GHz. <i>IEEE Journal of the Electron Devices Society</i> , 2021 , 9, 121-124	2.3	16
12	Wurtzite phonons and the mobility of a GaN/AlN 2D hole gas. <i>Applied Physics Letters</i> , 2019 , 114, 253501	3.4	14
11	Molecular beam epitaxial growth of scandium nitride on hexagonal SiC, GaN, and AlN. <i>Applied Physics Letters</i> , 2019 , 115, 172101	3.4	14
10	Molecular Beam Epitaxy Growth of Large-Area GaN/AlN 2D Hole Gas Heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900567	1.3	9
9	Terahertz spectroscopy of an electron-hole bilayer system in AlN/GaN/AlN quantum wells. <i>Applied Physics Letters</i> , 2017 , 111, 073102	3.4	8
8	High-conductivity polarization-induced 2D hole gases in undoped GaN/AlN heterojunctions enabled by impurity blocking layers. <i>Journal of Applied Physics</i> , 2021 , 130, 025703	2.5	7
7	GaN/AlN p-channel HFETs with $I_{max} > 420$ mA/mm and ~ 20 GHz f_T / f_{MAX} 2020 ,		6
6	Polarization-induced 2D hole gases in pseudomorphic undoped GaN/AlN heterostructures on single-crystal AlN substrates. <i>Applied Physics Letters</i> , 2021 , 119, 162104	3.4	6
5	In Situ Crystalline AlN Passivation for Reduced RF Dispersion in Strained-Channel AlN/GaN/AlN High-Electron-Mobility Transistors. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2100452	1.6	5
4	Very High Density ($> 10^{14}$ cm $^{-2}$) Polarization-Induced 2D Hole Gases Observed in Undoped Pseudomorphic InGaN/AlN Heterostructures. <i>Advanced Electronic Materials</i> , 2101120	6.4	3
3	(Invited) GaN-Based Multiple 2DEG Channel BRIDGE (Buried Dual Gate) HEMT Technology for High Power and Linearity. <i>ECS Transactions</i> , 2019 , 92, 103-108	1	2

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| 2 | Electric Fields and Surface Fermi Level in Undoped GaN/AlN Two-Dimensional Hole Gas Heterostructures. <i>Physica Status Solidi - Rapid Research Letters</i> , 2021 , 15, 2000573 | 2.5 | 2 |
| 1 | Quantitative scanning microwave microscopy of 2D electron and hole gases in AlN/GaN heterostructures. <i>Applied Physics Letters</i> , 2022 , 120, 012103 | 3-4 | 0 |